

C1206C105K5RECAUTO

ESD SMD Auto X7R, Ceramic, 1 uF, 10%, 50 VDC, X7R, SMD, MLCC, Temperature Stable, Electro Static Discharge, Automotive Grade, 1206



Click here for the 3D model.

Dimensions	
Chip Size	1206
L	3.2mm +/-0.25mm
W	1.6mm +/-0.2mm
т	1mm +/-0.10mm
В	0.5mm +/-0.25mm

ackaging Specifications	
Packaging	T&R, 180mm, Plastic Tape
Packaging Quantity	2500

General Information	
Series	ESD SMD Auto X7R
Style	SMD Chip
Description	SMD, MLCC, Temperature Stable, Electro Static Discharge, Automotive Grade
Features	Temperature Stable, Automotive Grade
RoHS	Yes
Termination	Tin
Marking	No
Qualifications	AEC-Q200
AEC-Q200	Yes
Component Weight	25 mg
Shelf Life	78 Weeks
MSL	1

Specifications			
Capacitance	1uF		
Measurement Condition	1 kHz 1.0Vrms		
Capacitance Tolerance	10%		
Voltage DC	50 VDC		
ESD Level per AEC-Q200	25,000 V ESD Level		
Dielectric Withstanding Voltage	125 VDC		
Temperature Range	-55/+125°C		
Temperature Coefficient	X7R		
Capacitance Change with Reference to +25°C and 0 VDC Applied (TCC)	15%, 1kHz 1.0Vrms		
Dissipation Factor	2.5%1kHz1.0Vrms		
Aging Rate	3% Loss/Decade Hour: Referee Time is 1000 Hours		
Insulation Resistance	500 MOhms		

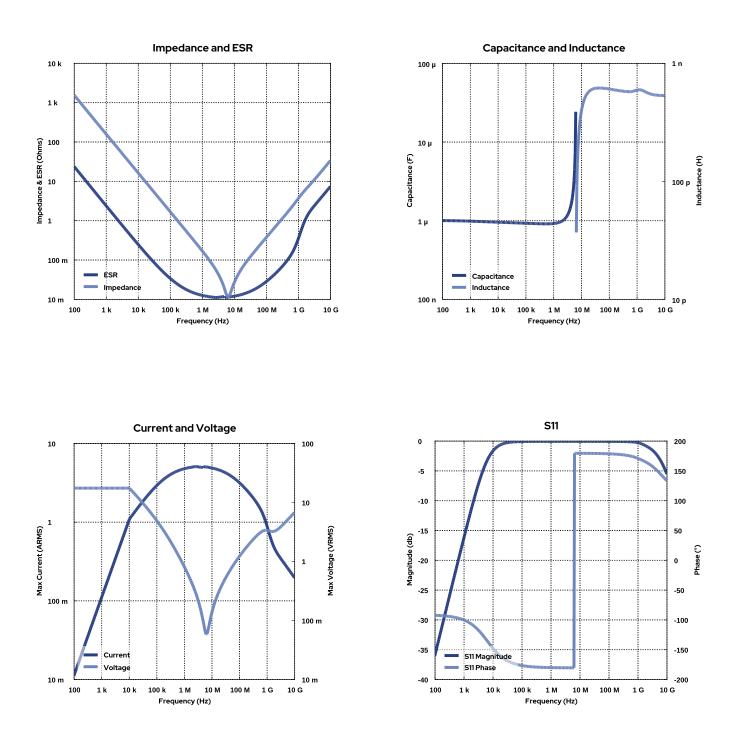
Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute - and we specifically disclaim - any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.



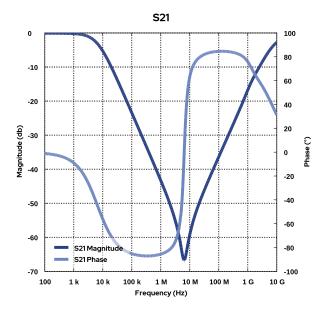
C1206C105K5RECAUTO ESD SMD Auto X7R, Ceramic, 1 uF, 10%, 50 VDC, X7R, SMD, MLCC, Temperature Stable, Electro Static Discharge, Automotive Grade, 1206

## Simulations

For the complete simulation environment please visit K-SIM.







Capacitance Change vs. DC Voltage Bias 0 -10 -20 Capacitance Change (%) -30 -40 -50 -60 -70 Vbias ¢ap Change -80 5 15 0 10 20 25 30 35 40 45 50 Voltage (VDC)

**Capacitance Change versus Temperature** 0.5 0 -0.5 -1 Capacitance Change (%) -1.5 -2 -2.5 -3 -3.5 -4 -4.5 Temp Cap Change -60 -40 -20 0 20 40 60 80 100 120 140 Temperature (C)

Capacitance Change versus AC Voltage 8 6 4 Capacitance Change (%) 2 0 -2 -4 VCAC Cap Change -6 0.5 1.5 2 2.5 0 1 Voltage (VAC)



## These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.
- The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
- The effects shown herein are based on measured data from a multiple part sample of the parts in question.
- Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance. The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages generated at any other
- harmonics.
- Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

All Information given herein is believed to be accurate and reliable, but is presented without guarantee, warranty, or responsibility of any kind, expressed or implied. Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute – and we specifically disclaim – any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.

If you have any questions please contact K-SIM.